

COMPLIANT

HALOGEN

FREE



Precision Monolithic Quad SPST **Low-Voltage CMOS Analog Switches**

DESCRIPTION

The DG441L, DG442L are low voltage pin-for-pin compatible companion devices to the industry standard DG441L, DG442L with improved performance.

Using BiCMOS wafer fabrication technology allows the DG441L, DG442L to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with \pm 3 V to \pm 6 V.

Combining high speed (ton: 20 ns), flat RDS(on) over the analog signal range (5 Ω), minimal insertion lose (- 3 dB at 280 MHz), and excellent crosstalk and off-isolation performance (-50 dB at 50 MHz), the DG441L, DG442L are ideally suited for audio and video signal switching.

The DG441L, DG442L responds to opposite control logic as shown in the Truth Table open and two normally closed switches.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- 2.7 V thru 12 V single supply or ± 3 V thru ± 6 V dual supply
- On-resistance $R_{DS(on)}$: 17 Ω
- Fast switching t_{ON}: 20 ns
 - t_{OFF}: 12 ns
- TTL, CMOS compatible
- Low leakage: 0.25 nA
- 2000 V ESD protection
- Compliant to RoHS Directive 2002/95/EC

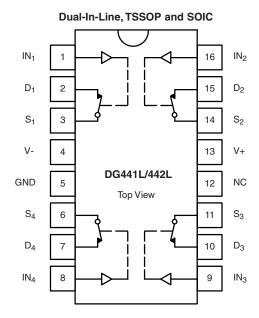
BENEFITS

- Widest dynamic range
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing

APPLICATIONS

- Precision automatic test equipment
- Precision data acquisition
- Communication systems
- Battery powered systems
- Computer peripherals
- SDSL, DSLAM
- Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE							
Logic	DG441L	DG442L					
0	On	Off					
1	Off	On					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION							
Temp. Range	Package	Part Number					
- 40 °C to 85 °C	16-pin TSSOP	DG441LDQ-T1-E3					
	10-ріп 1330ғ	DG442LDQ-T1-E3					
	16-pin narrow	DG441LDY-T1-E3					
	SOIC	DG442LDY-T1-E3					
	16-pin CerDIP	DG441LAK, DG441LAK/883					
- 55 °C to 125 °C	16-pill CelDIP	DG442LAK, DG442LAK/883					
	LCC-20	DG441LAZ/883					
	LOG-20	DG442LAZ/883					

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DG441L, DG442L

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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
V + to V -			- 0.3 to 13				
GND to V - A			7	V			
Digital Inputs ^a V _S , V _D			GND - 0.3 to (V +) + 0.3 or 30 mA, whichever occurs first	-			
Continuous Current (any terminal)			30	mA			
Current, S or D (pulsed 1 ms, 10 % d	uty cycle)		100	1 111/2			
Storage Temperature	(DQ, DY suffix)		- 65 to 125	°C			
Storage remperature	(AK suffix)		- 65 to 150	1			
	16-pin TSSOP ^c		450				
Power Dissipation (Packages) ^b	16-pin narrow Body SOIC ^d		650	mW			
	16-pin CerDIP ^e		900				

- Notes: a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.

- c. Derate 7 mW/°C above 75 °C d. Derate 7.6 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C.

SPECIFICATIONS ^a (Si	rigie Sup	Test Conditions			A Suffix Limits		D Suffix	Limits	
		Unless Otherwise Specified V + = 12 V, V - = 0 V			- 55 °C to 125 °C				Unit
Parameter	Symbol	$V_{IN} = 12 \text{ V}, V_{I} = 0 \text{ V}$ $V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$	Temp.b	Typ.c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	
Analog Switch									
Analog Signal Range ^e	V_{ANALOG}		Full		0	12	0	12	٧
Drain-Source On-Resistance	R _{DS(on)}	V += 10.8 V, V -= 0 V $I_S = 10 \text{ mA}, V_D = 2/9 \text{ V}$	Room Full	20		30 45		30 40	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	I _S = 10 mA, V _D = 9 V	Room	0.1		0.5		0.5	52
Switch Off Leakage Current	I _{S(off)}		Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Owner On Leakage Ouriert	I _{D(off)}		Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current	I _{D(on)}	$V_S = V_D = 11/1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V _{IN} Low	I _{IL}	V _{IN} Under Test = 0.8 V	Full	0.01	- 1.5	1.5	- 1	1	μA
Input Current, V _{IN} High	I _{IH}	V _{IN} Under Test = 2.4 V	Full		- 1.5	1.5	- 1	1	μΛ
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$	Room Full	20		60 80		60 70	ns
Turn-Off Time	t _{OFF}	$V_S = 5 \text{ V}$, see figure 2	Room Full	12		35 50		35 45	113
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	5					рC
Off Isolation ^e	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room	71					dB
Channel-to-Channel Crosstalke	X _{TALK}	11[= 30 s2, O[= 3 pi , i = 1 ivii iz	Room	95					uБ
Source Off Capacitance ^e	C _{S(off)}		Room	5					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	6					pF
Channel On Capacitance ^e	C _{D(on)}		Room	15					
Power Supplies									
Positive Supply Current	l+		Full	0.03		1.5		1	
Negative Supply Current	l-	V _{IN} = 0 V or 12 V	Room Full	0.002	- 1 - 7.5		- 1 - 5		μΑ
Ground Current	I _{GND}		Full	0.002	- 1.5		- 1		



SPECIFICATIONS ^a (Dual Supply ± 5 V)									
		Test Conditions Unless Otherwise Specified			A Suffix Limits		D Suffi - 40 °C	to 85 °C	Unit
Parameter	Symbol	V += 5 V, V -= -5 V $V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Onne
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		- 5	5	- 5	5	V
Drain-Source On-Resistance	R _{DS(on)}	V += 5 V, V -= -5 V $I_S = 10 \text{ mA}, V_D = \pm 3.5 V$	Room Full	20		33 45		33 40	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 10 \text{ mA}, V_D = \pm 3.5 \text{ V}$	Room	0.1		0.5		0.5	52
Switch Off	I _{S(off)}	V + = 5.5 , V - = - 5.5 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current ^g	I _{D(off)}	$V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current ^g	I _{D(on)}	V += 5.5 V, V -= -5.5 V $V_S = V_D = \pm 4.5 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control	•		•						
Input Current, V _{IN} Low ^e	I _{IL}	V _{IN} Under Test = 0.8 V	Full	0.05	- 1.5	1.5	- 1	1	
Input Current, V _{IN} High ^e	I _{IH}	V _{IN} Under Test = 2.4 V Full	Full	0.05	- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics			•	1	1				l
Turn-On Time	t _{ON}	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$	Room Full	21		60 83		60 70	ns
Turn-Off Time	t _{OFF}	$V_S = \pm 3.5 \text{ V}$, see figure 2	Room Full	16		35 55		35 45	110
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	5					рC
Off Isolation ^e	OIRR		Room	68					
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 Ω$, $C_L = 5 pF$, $f = 1 MHz$	Room	85					dB
Source Off Capacitance ^e	C _{S(off)}		Room	9					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	9					pF
Channel On Capacitance ^e	C _{D(on)}		Room	20					
Power Supplies									
Positive Supply Current ^e	I+		Full	0.002		1.5		1	
Negative Supply Current ^e	-	V _{IN} = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μΑ
Ground Current ^e	I _{GND}		Full	- 0.002	- 1.5		- 1		

DG441L, DG442L

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SPECIFICATIONS ^a (Single Supply 5 V)									
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C			k Limits to 85 °C	Unit
Parameter	Symbol	V += 5 V, V -= 0 V $V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Oiiit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full			5		5	V
Drain-Source On-Resistance ^e	R _{DS(on)}	V += 4.5 V $I_S = 5 \text{ mA}, V_D = 1 V, 3.5 V$	Room Full	35		50 88		50 75	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	I _S = 10 mA, V _D = 3.5 V	Room	0.5		1		1	52
Dynamic Characteristics									
Turn-On Time ^e	t _{ON}	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$	Room Hot	27		50 90		50 60	ns
Turn-Off Time ^e	t _{OFF}	$V_S = 3.5 \text{ V}$, see figure 2	Room Hot	15		30 55		30 40	115
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	0.5					рC
Power Supplies	Power Supplies								
Positive Supply Current ^e	I+		Full	10		200		100	
Negative Supply Current ^e	1-	V _{IN} = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μΑ
Ground Current ^e	I _{GND}		Full	- 10	- 200		- 100		





SPECIFICATIONS ^a (Single Supply 3 V)									
		Test Conditions Unless Otherwise Specified V + = 3 V, V - = 0 V			A Suffix Limits - 55 °C to 125 °C		D Suffix - 40 °C		Unit
Parameter	Symbol	V + = 3 V, V - = 0 V $V_{IN} = 0.4 V^{f}$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	
Analog Switch	1		l						
Analog Signal Range ^e	V _{ANALOG}		Full		0	3	0	3	V
Drain-Source On-Resistance	R _{DS(on)}	V += 2.7 V, V -= 0 V $I_S = 5 mA, V_D = 0.5, 2.2 V$	Room Full	65		80 115		80 100	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 5 \text{ mA}, V_D = 2.2 \text{ V}$	Room	1		3		3	52
Switch Off	I _{S(off)}	V + = 3.3 , V - = 0 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current ^g	I _{D(off)}	$V_D = 1, 2 V, V_S = 2, 1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current ^g	I _{D(on)}	V += 3.3 V, V -= 0 V $V_S = V_D = 1, 2 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control	1		l					l	l
Input Current, V _{IN} Low ^e	I _{IL}	V _{IN} under test = 0.4 V	Full	0.005	- 1.5	1.5	- 1	1	
Input Current, V _{IN} High ^e	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$	Room Full	50		136 175		136 151	ns
Turn-Off Time	t _{OFF}	$V_S = 1.5 V$, see figure 2	Room Full	30		100 140		100 125	113
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	1					рC
Off Isolation ^e	OIRR		Room	68					
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	85					dB
Source Off Capacitance ^e	C _{S(off)}		Room	6					
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	6					pF
Channel On Capacitance ^e	C _{D(on)}		Room	20					

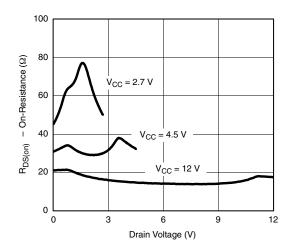
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

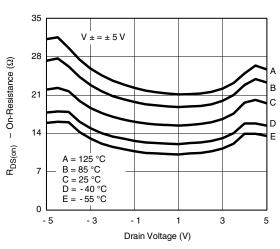
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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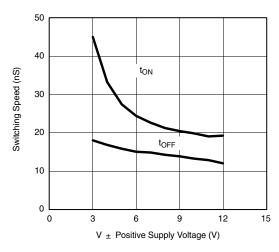
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



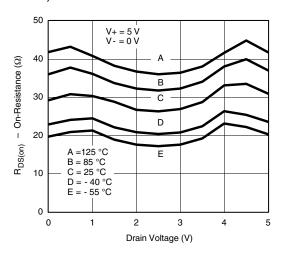
R_{DS(on)} vs. Drain Voltage (Single Supply)



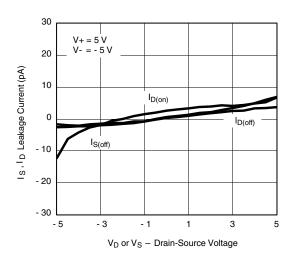
R_{DS(on)} vs. Drain Voltage and Temperature (Dual Supply)



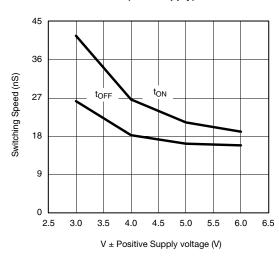
Switching Time vs. Single Supply



 $R_{DS(on)}$ vs. Drain Voltage and Temperature (Single Supply)



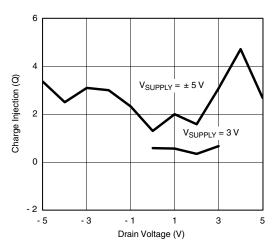
Leakage Current vs. Analog Voltage (Dual Supply)



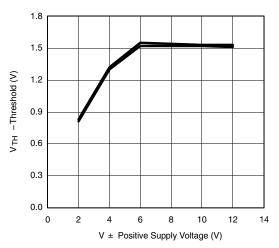
Switching Time vs. Dual Supply



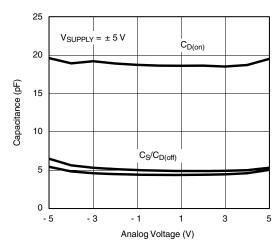
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



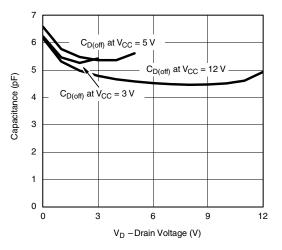
Charge Injection vs. Drain Voltage



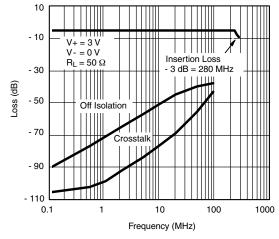
Input Threshold vs. Single Supply Voltage



Capacitance vs. Analog Signal (Dual Supply)

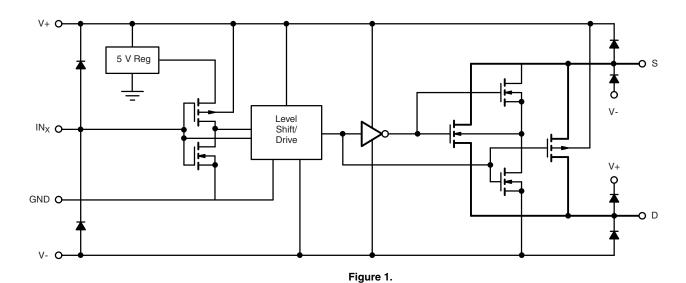


Drain Capacitance vs. Drain Voltage (Single Supply)



Insertion Loss, Off Isolation and Crosstalk vs. Frequency (Single Supply)

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)



TEST CIRCUITS

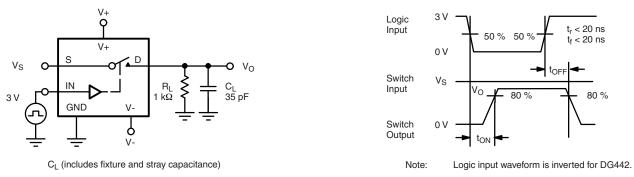


Figure 2. Switching Time

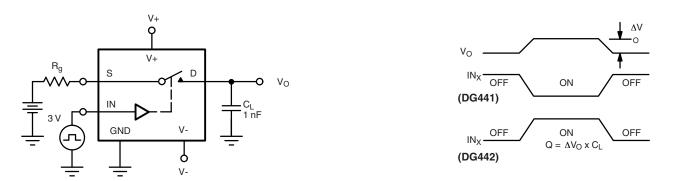


Figure 3. Charge Injection



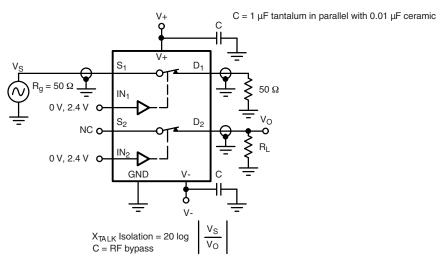


Figure 4. Crosstalk

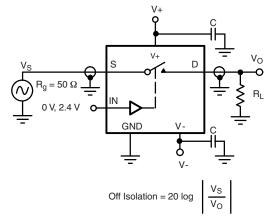


Figure 5. Off Isolation

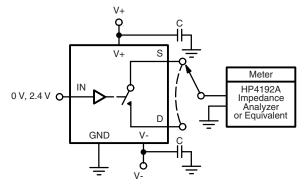
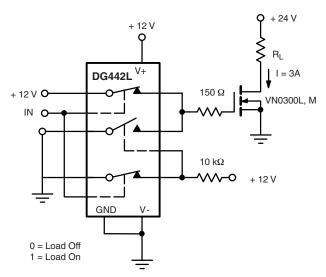


Figure 6. Source/Drain Capacitances

APPLICATIONS





1/4 DG442L S D C_H + V_{OUT} IN O H = Sample L = Hold

Figure 7. Power MOSFET Driver

Figure 8. Open Loop Sample-and-Hold

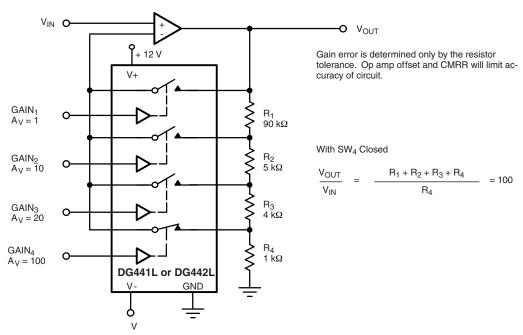
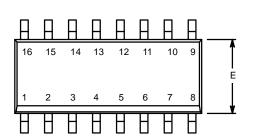


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71399.



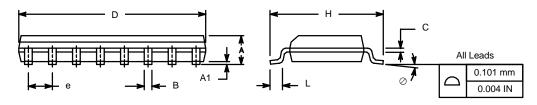
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIM	IETERS	INC	HES				
Dim	Min	Max	Min	Max				
Α	1.35	1.75	0.053	0.069				
A ₁	0.10	0.20	0.004	0.008				
В	0.38	0.51	0.015	0.020				
С	0.18	0.23	0.007	0.009				
D	9.80	10.00	0.385	0.393				
E	3.80	4.00	0.149	0.157				
е	1.27	BSC	0.050	BSC				
Н	5.80	6.20	0.228	0.244				
L	0.50	0.93	0.020	0.037				
0	0°	8°	0°	8°				
FCN: S-0	FCN: S-03946—Rev. F. 09-Jul-01							

ECN: S-03946—Rev. F, 09-Jul-01

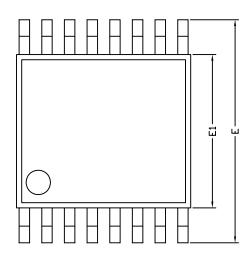
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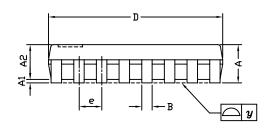


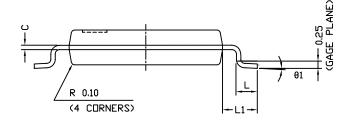
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



TSSOP: 16-LEAD







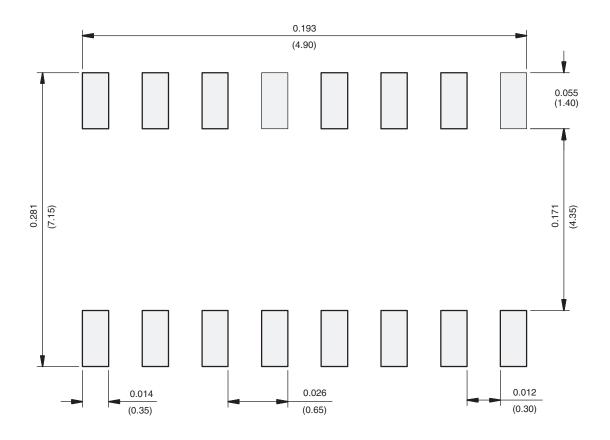
	DIMENSIONS IN MILLIMETERS						
Symbols	Min	Nom	Max				
Α	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	=	1.00	1.05				
В	0.22	0.28	0.38				
С	=	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	=	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D. 23-0	Oct-06						

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



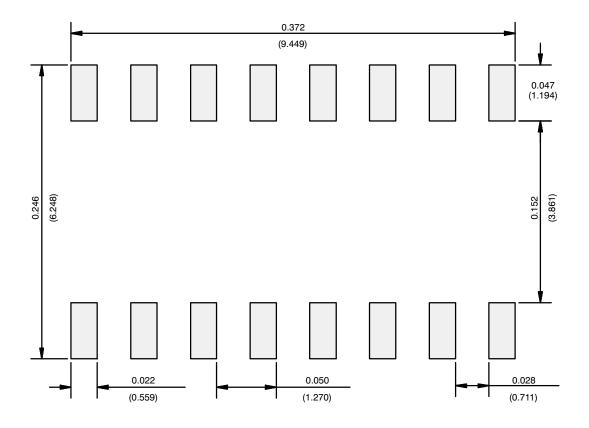
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

Legal Disclaimer Notice



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